

IRLZ34PBF-VB Datasheet

N-Channel 60 V (D-S) MOSFET

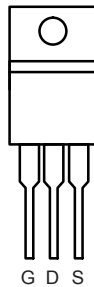
PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a
60	0.024 at V _{GS} = 10 V	50
	0.028 at V _{GS} = 4.5 V	40

FEATURES

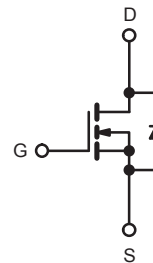
- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Logic-Level Gate Drive
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC



TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	V _{DS}		60	V
Gate-Source Voltage	V _{GS}		± 20	
Continuous Drain Current ^f	V _{GS} at 10 V	T _C = 25 °C	I _D	50
Continuous Drain Current			T _C = 100 °C	36
Pulsed Drain Current ^a			I _{DM}	200
Linear Derating Factor				1.0
Linear Derating Factor (PCB Mount) ^e				0.025
Single Pulse Avalanche Energy ^b			E _{AS}	400
Maximum Power Dissipation	T _C = 25 °C		P _D	150
Maximum Power Dissipation (PCB Mount) ^e	T _A = 25 °C			3.7
Peak Diode Recovery dV/dt ^c			dV/dt	4.5
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 175
Soldering Recommendations (Peak Temperature) ^d	for 10 s			300 ^d

Notes

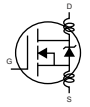

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 25 V, starting T_J = 25 °C, L = 179 μH, R_g = 25 Ω, I_{AS} = 51 A (see fig. 12).
- I_{SD} ≤ 51 A, di/dt ≤ 250 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 175 °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).
- Current limited by the package, (die current = 51 A).

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

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SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	60	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.070	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0	-	2.5		
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 10\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA	
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 21\text{ A}^b$	-	0.024	-	Ω
		$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}^b$	-	0.028	-	
Forward Transconductance	g_{fs}	$V_{DS} = 25\text{ V}, I_D = 21\text{ A}^b$	23	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5	-	190	-	pF	
Output Capacitance	C_{oss}		-	920	-		
Reverse Transfer Capacitance	C_{rss}		-	170	-		
Total Gate Charge	Q_g	$V_{GS} = 5.0\text{ V}$	$I_D = 51\text{ A}, V_{DS} = 48\text{ V},$ see fig. 6 and 13 ^b	-	-	66	nC
Gate-Source Charge	Q_{gs}			-	-	12	
Gate-Drain Charge	Q_{gd}			-	-	43	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, I_D = 51\text{ A},$ $R_g = 4.6\text{ }\Omega, R_D = 0.56\text{ }\Omega,$ see fig. 10 ^b	-	17	-	ns	
Rise Time	t_r		-	230	-		
Turn-Off Delay Time	$t_{d(off)}$		-	2	-		
Fall Time	t_f		-	110	-		
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	50°	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	200	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 51\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	2.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 51\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	130	180	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.84	1.3	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- c. Current limited by the package, (Die Current = 51 A).

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



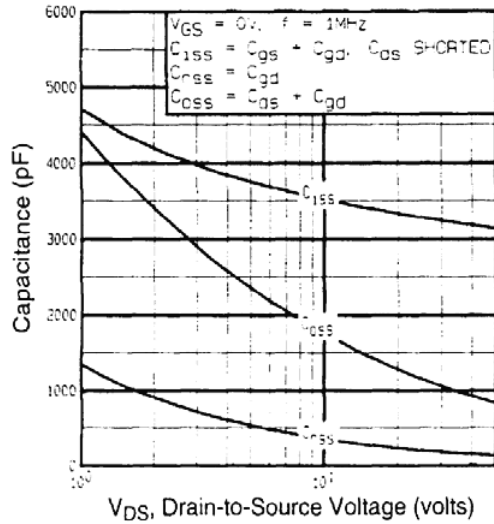


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage

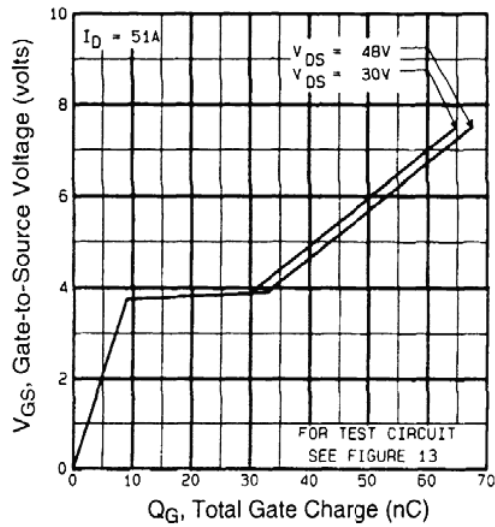


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature

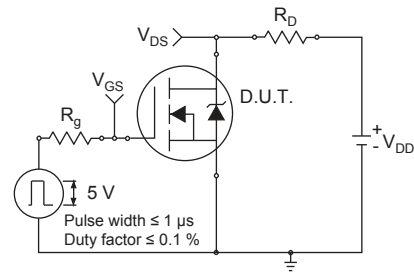


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

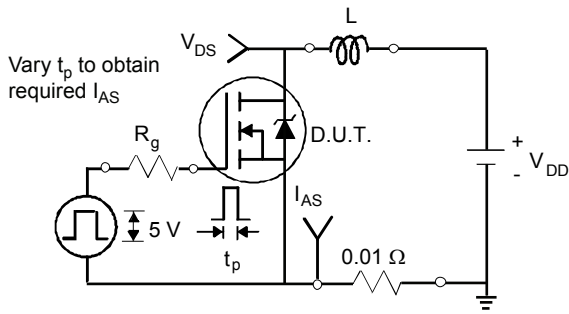


Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

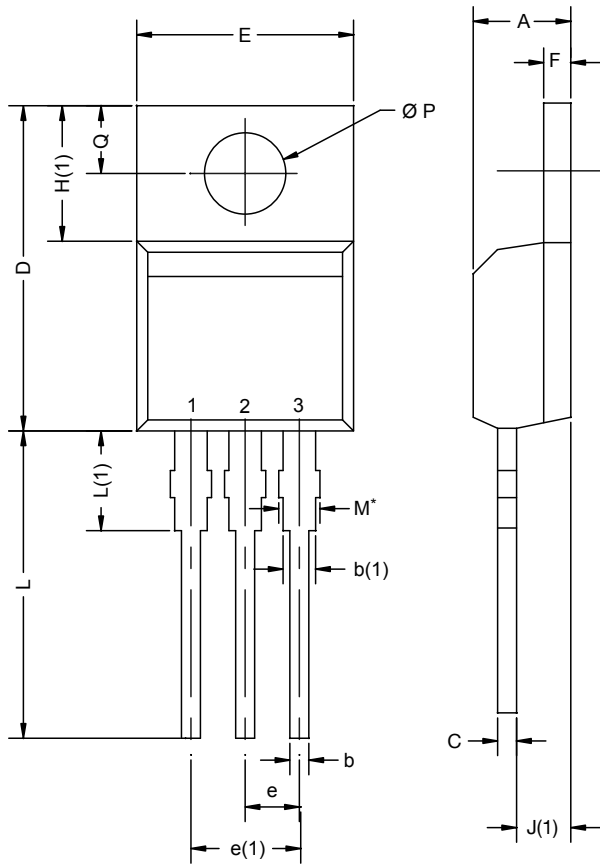


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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